# Low tem perature transport through a quantum dot: nite-U results and scaling behavior

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W e calculate the conductance through a quantum dot weakly coupled to m etallic leads, m odeled by the spin-1/2 Anderson model with nite Coulomb repulsion U. We adopt the non-crossing approximation method in its nite-U extension (UNCA). Our results can be compared to those obtained with the exact num erical renormalization group method, and good agreement is found both in the high temperature (Coulomb blockade) and in the low temperature (Kondo) regime. W e analyze the scaling properties of the low temperature conductance, and calculate the universal function which describes the electronic transport in the Kondo regime. Very good agreement with recent experim ental results is found. Finally, we suggest a simple interpolating function which ts fairly well the calculated conductance in a broad tem perature range.

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#### I. IN TRODUCTION

The Kondo e ect, a phenomenon discovered in the late 30s in diluted magnetic alloys, plays a crucial role in the low temperature properties of many strongly correlated systems, such as Ce, Y and U compounds. Very recently Kondo-like phenomena were also observed in the low-temperature transport properties of quantum dot devices, $^{2{9}}$  opening new opportunities to control the K ondo e ect experim entally, and starting a new research. 10

A quantum dot device consists of a small sized quantum dot (QD) weakly connected by tunnel barriers to two electrodes, called source and drain. In this system the QD may be considered as an articial atom, in which a well de ned number of electrons, n, is con ned. The energy required to add a new electron to the QD is  $U = e^2 = 2C$ , where C is the capacitance of the QD itself. The energy U is determined by the Coulomb repulsion between two electrons in the QD and thus it scales with the inverse of the dot dim ensions. Therefore, in small sized QD, U is usually larger than the coupling to the leads. An important aspect of a QD device is that the energy of electrons in the dot can be tuned by a gate voltage. Increasing the gate voltage, the energy necessary to add a new electron decreases, eventually making the addition possible. Thus it was shown that, at low tem perature, the transport of electrons through the QD is allowed only at those values of the gate voltage at which the state with n electrons is realized and that with n + 1 electrons becom es suddenly energetically accessible (Coulom b blockade). 11;12

The idea that Kondo-like phenomena should appear in such a system at very low temperature can be traced back to 1988. In that year it was recognized that the An-

derson model, introduced in 1961 to describe a magnetic im purity in a m etal, $^{13}$  could also be applied to a Q D coupled to its leads. 14;15 Soon afterwards several theoretical studies have been devoted to analyze the properties of such a system (see e.g. Refs. 16(23). It was predicted that at very low tem perature (T  $T_K$ , where  $T_K$  is the K ondo tem perature) a narrow peak should appear in the local density of states, close to the Ferm i level. Thus, states belonging to opposite electrodes should m ix easier than at high temperature (T  $T_K$  ), and the conductance should increase. In addition, the K ondo anom alies were predicted to appear only for odd  $n_{i}^{14}$  and thus only if the total spin of the electrons in the QD, S, is half integer. These predictions are now con med by several experim ental results. The K ondo tem perature of Q D devices is however very small (usually less than a few hundred m K) compared to the one of diluted magnetic alloys (usually a few K). Recently, 8;9 in some QD devices K ondo anom alies have been observed for even n as well; it is believed that these deviations from the even/odd n e ect are related to the form ation of integer spin states with S

In the present paper we will focus our attention on those OD devices for which the K ondo e ect occurs only for odd n. The transport properties of such a QD device have been calculated by using many dierent approaches, such as the equations of motion method,  $^{17}$  the non-crossing approximation  $(NCA)^{19;20}$  and the exact num erical renorm alization group (NRG) technique.  $^{21}\{23$ Within the NRG it was possible to calculate the conductance as a function of the gate voltage, and thus to obtain { in the case S = 1=2 { the even/odd e ect in very good agreem ent with experim ental results. Sim ilar results were also obtained with the approximate equations of motion method and with the NCA. The latter m ethod<sup>24;25</sup> was applied to low temperature transport of a QD in the in nite U lim it and thus the even/odd alternation e ect was obtained<sup>20</sup> for n switching from n=0 to n=1.

Even if approximated, the NCA can be easily extended to models in which the realistic levels structure of the QD is kept into account (i.e. in the presence of several levels and possibly of an external magnetic eld), thus becomping a very convenient method for a direct comparison to transport properties of realQD devices. As a matter of fact, the NCA was used with success to study, e.g., orbital degeneracy elects in diluted magnetic alloys.  $^{24}\{^{26}$  However, in the case of QD devices, it is rst necessary to go beyond the U  $\,!\,1\,$  condition, which does not account for the even/odd elect for all values of n  $\,!\,1\,$ 

In the present work we apply the <code>nite-U</code> NCA method<sup>27</sup> to the QD device system , modeled by the spin-1/2 A nderson model. We calculate the conductance as a function of the position of the QD level, and study the system in the empty orbital, mixed valence and K ondo regimes. Our results are in good agreement with the exact numerical renormalization groupones. In particular, we obtain the correct behavior of the conductance both in the high temperature regime, T  $_{\rm K}$ , in which the conductance shows the C oulomb b blockade peaks, and the low temperature regime, T <  $_{\rm K}$ , where the conductance increases for odd n due to the K ondo e ect.

The paper is organized as follows. In section II we describe the model Ham iltonian and give a short introduction to the nite-U NCA. In section III we show and discuss the numerical results, in particular the linear-response conductance, which we compare to exact results and to experimental data. In section IV we study the scaling behavior of the conductance as a function of temperature, and we suggest an empirical formula which is valid both in the Fermi-liquid and in the T  $_{\rm K}$  temperature regime, where the conductance has a logarithm ic behavior.

### II.M ODEL AND METHOD

### A . H am iltonian

In order to describe a quantum dot (Q D ) coupled with its leads we adopt the Anderson H am iltonian  $^{15}$ 

$$H = \begin{cases} X & X & X \\ {}^{1}_{k} c_{k}^{y} c_{k} + {}^{1}_{0} & d^{y}d + U n_{d} n_{d} \end{cases}$$

$$+ V_{k} c_{k}^{y} d + h c : : (1)$$

Here  $c_k^y$  ( $c_k$ ) creates (destroys) a conduction electron with momentum k and spin in one of the two leads, which we label with S (source) and D (drain);  $d^y$  (d) creates (destroys) an electron with spin on the quantum dot; " $_0$  is the energy of a single electron localized on

the QD and U is the Coulomb interaction among electrons in the dot;  $n_{\rm d}=d^{\rm y}\,d$  is the number of electrons operator for a given spin in the QD;  $V_k$  is the hybridization between the leads and the QD states, whosem odulus is supposed to be k-independent, with  ${\bf j}V_k$   $j=V_{S\,(D\,)}$  for (k; ) 2 S (D). The lead-dot coupling strengths are given by

$$V_{S(D)}^{2}$$
  $V_{S(D)}^{2}$   $V_{K}^{2}$  (" ";): (2)

It was shown<sup>15</sup> { through a unitary transform ation of the band states { that the H am iltonian (1) is equivalent to a two band A nderson m odel in which the rst band does not interact with the QD, and the second is coupled to the quantum dot states through the hybridization V =  $\frac{1}{V_S^2 + V_D^2}$ . Thus the problem of calculating the transport properties of H am iltonian (1) is reduced to the problem of calculating the spectral properties of the one band A nderson m odel, provided that the actual lead-dot coupling strength is given by<sup>28</sup>

$$= _{S} + _{D} = _{N} ("_{F}) V^{2};$$
 (3)

where N (" $_{\rm F}$ ) is the density of states (per spin) of the leads at the Ferm i level, " $_{\rm F}$ . It is reasonable to approxim ate the conduction bands of the leads with those of a non interacting two dimensional Ferm i gas. Thus the density of states (DOS) per spin may be written as N (") = 1=2D , where D is one half of the band-width, therefore = V  $^2$ =2D .

The main dierence between the Anderson modelused in the ordinary K ondo problem and the one used here is the following. In the present model the energy dierence  $\textbf{"}_0$   $\textbf{"}_F$  is not xed, but, on the contrary, it can be tuned by a gate voltage  $V_g$ , coupled to the QD through a capacitor. From now on we set the Fermilevel  $\textbf{"}_F=0$ . In rst approximation, we can assume that  $\textbf{"}_0$  increases linearly with  $eV_g$  (with common conventions for the sign of gate voltage). Thus the equilibrium thermodynamic properties of the system described by the Hamiltonian (1) are functions of two external parameters: the temperature T and the gate voltage  $V_g$ .

### B. Linear response conductance

In the linear response regim e ( $V_{S\,D}$   $V_g$ , where  $V_{S\,D}$  is the source-drain voltage), the conductance of the system QD+ leads, G, m ay be written in a Landauer-like form  $^{17;18}$ 

G (T; V<sub>g</sub>) = 
$$\frac{2e^2}{h}^{Z+1}$$
  $\frac{1}{2}$  Im fG<sup>R</sup> ("+i)g  $\frac{ef}{e}$  d"; (4)

where for simplicity we assume that the couplings to the leads are symmetric ( $_{\rm S}$  =  $_{\rm D}$ ). Here f is the

Ferm i distribution function and  $G^R$  (" + i ) is the retarded local G reen function, i.e. the Fourier transform of  $G^R$  (t) i (t)hfd(t);d'(0)qi.

The quantity Im  $G^R$  ("+ i) in Eq. (4) is proportional to the local density of states, ("), de ned as

(") 
$$\frac{1}{2} \text{ Im } G^{R} ("+i) : (5)$$

W e point out that the e ects of the C oulom b interaction among electrons in the QD are contained in the local density of states. The main purpose of this work is thus to calculate (") as a function of temperature and gate voltage, and the resulting linear conductance.

#### C.Number of electrons

The low temperature transport properties of a mesoscopic system such as the QD+ leads previously described are characterized by the phenomenon of charge quantization. When Coulomb blockade occurs the number of electrons in the QD is a xed integer. This number can be changed by raising the voltage of the gate electrode. In this way the energy of the electrons in the QD is lowered with respect to the Fermienergy in the leads. The change in energy necessary to add a new electron is U. This may be seen as the energy required to charge the QD,  $e^2=2C$ , where C is the capacitance of the QD. Thus the average number of electrons on the QD, hni, with

is an important quantity in this problem (here N is the degeneracy of  $\textbf{\textit{"}}_0$  and in the present case N = 2). The number of electrons is | like the conductance | a function of the local density of states.

### D . F in ite-U non-crossing approxim ation

In order to calculate ("), the local DOS for the single impurity Anderson model, we adopt the nite-U non-crossing approximation (UNCA) approach, 27 an extension of the non-crossing approximation (NCA) to the nite U Anderson model. We point out that a nite U treatment is necessary in order to calculate the correct behavior of the conductance as a function of the gate voltage (and thus of the number of electrons on the QD).

The NCA is a diagram m atic technique introduced for the Anderson model in the U  $\,!\,$  1  $\,$  lim it.  $^{24;25}$  The main idea of the NCA is that the self-energy can be expanded in a series of diagram s of order V  $^2$ =N , where N is the degeneracy of the local level, usually large for K ondo in purities in diluted magnetic alloys (e.g. N = 6 for Ce impurities). The non-crossing diagram s are sum med up to all orders, and the  $\,$ rst neglected diagram s are of order (V  $^2$ =N ) $^2$ . The NCA was proved to be successful?

already for N = 2. Thus it was applied with good results also to the spin-1/2 U ! 1 Anderson model out of equilibrium  $,^{19;20}$  e.g. it was used to calculate the behavior of the conductance as a function of the chemical potential in the QD+ leads problem .

The NCA and the UNCA lead to a set of integral equations for the self energy, which have to be solved self-consistently. The number of equations depends on the number of many body states for the electrons in the QD. If U is nite there are four possible manybody states, namely  $\mathfrak{P};0$  i (with energy " = 0),  $\mathbb{1};\mathbb{1};\mathbb{1}$  in (degenerate, with energy " = "0), and  $\mathbb{1};\mathbb{1};\mathbb{1}$  is (degenerate, with energy " = "0), and  $\mathbb{1};\mathbb{1};\mathbb{1}$  is (with energy " = 2"0 + U). For each state a self energy and a ionic propagator are introduced. Thus we have three self energies, 0, 1, 2 and three propagators,  $\mathbb{G}_0$ ,  $\mathbb{G}_1$ ,  $\mathbb{G}_2$  (due to spin degeneracy  $\mathbb{G}_{1}$  =  $\mathbb{G}_{1}$  =  $\mathbb{G}_1$  and  $\mathbb{I}$  =  $\mathbb{I}$  = 1 = 1). The UNCA equations may then be written as  $^{27;30}$ 

with

$$G_0(! + i) = [! + i \quad _0(! + i)]^1;$$
 (10)

$$G_1(! + i) = [! + i \quad "0 \quad _1(! + i)]^1;$$
 (11)

$$G_2(!+i) = [!+i 2" U_2(!+i)]^1 : (12)$$

In the in nite U  $\lim$  it, the double occupation state is forbidden, and  $G_2$  m ay be neglected.

Once this system of six equations is solved, it is possible to express all the physical quantities in terms of the ionic resolvents. In particular the retarded local G reen function may be evaluated by analytic continuation from the corresponding in aginary time propagator, which may be written as<sup>27</sup>

$$G (i!) = \frac{1}{Z} \int_{C}^{I} \frac{dz}{2 i} e^{z=k_B T}$$

$$[G_0(z)G_1(z+i!) + G_1(z)G_2(z+i!)]; \quad (13)$$

where Z is the QD partition function, i.e.

$$Z = \int_{C}^{I} \frac{dz}{2 i} e^{z=k_B T} [G_0(z) + G_1(z) + G_2(z)]$$
 (14)

Finally, the local density of states of the QD can be obtained from the retarded local G reen function through Eq. (5).

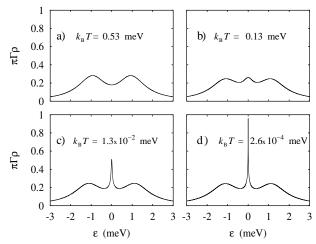


FIG.1. Equilibrium density of states for the particle-hole sym m etric A nderson m odel (U = 2" $_0$ ) at di erent tem peratures. Param eters: " $_0$  = 1 m eV , U = 2 m eV , = 0.35 m eV , D = 4 m eV . For  $k_B$  T = 2.6 10  $^4$  m eV (T = 3 m K) the local D O S at Ferm ienergy is (0) = 0.98. In this paper the Ferm i level " $_F$  is set equal to zero.

The NCA and the UNCA break down below a temperature T , which in the K ondo regime is much smaller than  $T_{\rm K}$ .  $^{24}$  Relow this temperature spurious features show up, e.g., in the local density of states. It is known that the exact results are recovered with the inclusion of vertex corrections,  $^{31}$  Relow within a set of integral equations which are numerically heavier than Eqs. (7-12). This is, however, beyond the purpose of the present paper. Here we will use the UNCA without vertex diagrams. We will see that, nevertheless, we can reproduce fairly well both the high and low temperature regimes, and that (above T ) the local DOS calculated with the UNCA is in good agreement with the exact numerical renormalization group (NRG) results.

# III. NUM ERICAL RESULTS

W e solve the self-consistent UNCA equations, and calculate the localDOS, by using the fast Fourier transforms technique. From (") we then obtain the Landauer conductance and the number of electrons as a function of the tem perature and of the position of the QD level, "0, proportional to  $V_{\!g}$ .

# ${\tt A}$ . Local density of states

The local density of states is shown in Fig. 1 as a function of the energy. The ratio %=2.85>1, and thus the m odel describes the system in the K ondo regime. For simplicity, we show the results for the particle-hole symmetric Anderson model (U = 2%). The K ondo temperature may be estimated from Haldane formula,  $^{34}$ 

$$k_B T_K$$
 (U =2)<sup>1=2</sup> exp [ "<sub>0</sub> ("<sub>0</sub> + U)=(2U )]; (15)

In the high tem perature lim it (T  $_{\rm K}$ , Fig. 1a), the local density of states show s two broad resonances. The rst one is located at energy "= E (n = 1) E (n = 0) ", the energy required to put the rst electron in the QD. The second resonance appears at "= E (n = 2) E (n = 1) ", + U, the energy required to add an additional electron. The shape of the resonance peaks is Lorentzian. The origin of the peak broadening is mainly the coupling QD-leads measured by the width , although a small thermal contribution is present since  $k_{\rm B}$  T & .

As the temperature decreases, a peak { which is the ngerprint of the K ondo e ect { appears close to the Ferm i level. The height of the peak increases on decreasing the temperature. Figure 1 shows that for T  $T_K$  the height of the K ondo peak tends to a maximum value, i.e. (" $_F = 0$ ) ! 1, which is reached exactly only at T = 0. At  $k_B$  T = 2.6  $10^4$  m eV (T= $T_K$  0.01, Fig. 1d) we nd (0) 0.98.

The evolution of (") as a function of tem perature is in fairly good agreement with the NRG results.  $^{21;23;35}$  In the very large U lim it we nd results consistent with those obtained by using the NCA method with in nite U  $^{24;25}$ .

# B. Linear-response conductance

The linear response conductance G and the average num ber of electrons hai are shown in Fig. 2 as a function 0.36 For 0.36in the dot is n 1, there are three relevant regimes of interest: the Kondo (K) regime < " $_0$  < U=2, the m ixed valence (M V ) regime  $j_0^{\dagger}j < j$  , and the empty orbital (EO) regime "0 < . In the opposite case  $^{"}_{0} > U = 2$ , when the number of electrons in the QD is 1, it is convenient to discuss the various regimes in terms of holes; thus the Kondo regime exists for , the mixed valence regime for "h < U j "U j < , and the empty orbital regime with n ' 2 occurs for  $"_0 > U + .$  These regimes are schematically indicated in Fig. 2b.

In the K ondo regime, we can extimate the K ondo temperature from Haldane formula, Eq. (15). We nd  $k_B T_K$   $10^5$   $10^2$  meV for 0.094 (Fig. 2a) and  $k_B T_K$  0.062 0.161 meV for 0.35 (Fig. 2b).

Figure 2a shows the results obtained for  $k_B\,\,T\,\,\,\,\,\,0.5$   $k_B\,\,T_K\,\,\,\,$ . In this lim it it was show  $n^{11;17}$  that the conductance has narrow peaks every time the average number of electrons in the QD increases by one. The peaks are separated by valleys in which the conductance is almost zero. This behavior (which is due to the Coulomb blockade  $^{12}$ ) is well reproduced in Fig. 2a. The peaks reach about

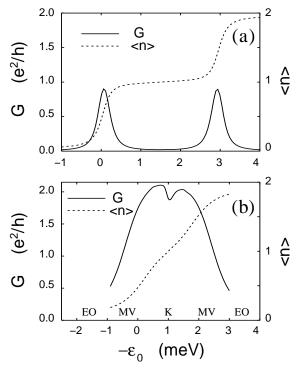


FIG. 2. Linear-response conductance G and average number of electrons on the dothni, for two dierent set of parameters: (a) Parameters are: = 0:094 m eV, D = 4 m eV, U = 3 m eV, and  $k_{\rm B}$  T = 4:3  $\,$  10  $^2$  m eV (T = 500 m K) (C oulom b blockade); (b) Parameters are: = 0:35 m eV, D = 4 m eV, U = 2 m eV, and  $k_{\rm B}$  T = 4:3  $\,$  10  $^4$  m eV (T = 5 m K). The various regimes as a function of  $\,$  " $_0$  are schematically indicated in (b) (see text).

 $e^2 \! = \! h$ , as expected from C oulomb blockade theory in the lim it  $k_B$  T  $\phantom{k_B}$ , and have a width of about 2 . This broadening is due to tunneling, while the thermal broadening is negligible. The line shape is almost Lorentzian. If the tem perature is raised so much that  $k_B$  T  $\phantom{k_B}$  the height of the peaks become smuch smaller than  $e^2 \! = \! h$  and their width is controlled by thermal broadening only.

Figure 2b shows G and hnifor T  $T_K$  . In this regim e, experiments $^{2}$  show that the valleys tend to raise when the number of electrons in the QD is odd, and remain alm ost unchanged when the number of electrons in the QD is even. In the very low temperature limit, the valleys with an odd number of electrons evolve into a plateau<sup>7</sup> at G 2e = h. This behavior is the manifestation of the Kondo e ect in the mesoscopic transport properties of the QD+leads system. Figure 2b shows that when hni 1 the conductance calculated with the UNCA tends to  $G = 2e^2 = h$ , while a valley appears for 2. Thus the Kondo regime is well 0 and hni hni described by the adopted method. The average number of electrons in Fig. 2b has a regular increase and does not have well de ned plateaux as in Fig. 2a, due to the larger value of .

Thus we have shown that the UNCA can describe well

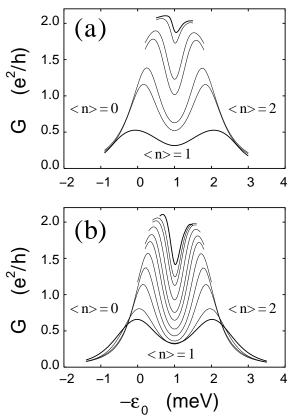


FIG .3. Linear response conductance as a function of "0 ("0 is always referred to the Ferm i level, being " $_{\rm F}$  = 0) the energy of the dot level with respect to the Ferm i energy, and for many temperatures. (a) Parameters: = 0.35 m eV, D = 4 m eV, U = 2 m eV. Temperatures (from the bottom to the top curve):  $k_{\rm B}$  T = 0.43, 0.086, 0.043, 8:6 10  $^3$ , 4:3 10  $^3$ , 8:6 10  $^4$ , and 4:3 10  $^4$  m eV. (b) Parameters: = 0.275 m eV, D = 4 m eV, U = 2 m eV. Temperatures (from the bottom to the top curve):  $k_{\rm B}$  T = 0.26, 0.17, 0.07, 0.035, 0.017, 8:6 10  $^3$ , 5:3 10  $^3$ , 2:6 10  $^3$ , 1:3 10  $^3$ , 8:6 10  $^4$ , and 4:3 10  $^4$  m eV.

both the Coulomb blockade and the Kondo e ect. The results can be compared with the exact NRG calculations. A green ent is very good in the Kondo regime, down to T  $0.01T_{\rm K}$ . In the mixed valence and empty orbital regimes the agreement decreases. At low temperature the UNCA breaks down and a spurious peak appears in the localDOS, close to the Fermilevel, as discussed for the usualNCA in Ref. 32. Within the parameters and the temperature chosen in Fig. 2b, this happens approximately for  $0.5\,{\rm m}\,{\rm eV}$  and  $0.5\,{\rm m}\,{\rm eV}$ . In this region the conductance calculated with the UNCA is much larger than the exact NRG result. Therefore from now on we will plot the conductance only for the values of T and  $0.0\,{\rm fm}\,{\rm eV}$  is reliable.

The linear-response conductance is shown in Fig. 3 as a function of  $"_0$  and for several di erent temperatures. The results are shown for two di erent choices

of the tunneling width: = 0.35 m eV (Fig. 3a) and = 0.275 m eV (Fig. 3b). In the K ondo regime, we estimate the K ondo tem perature by using H aldane form ula, and nd  $k_B\ T_K$  0.062 0.161 m eV for = 0.35 m eV and  $k_B\ T_K$  0.030 0.134 m eV for = 0.275 m eV .

Figure 3a shows that at high tem perature ( $k_B$  T >  $k_B$  T<sub>K</sub> ) there are two C oulomb blockade peaks at energy "0 0 and "0 U, them axim um value of the conductance being G 0.5e²=h. As the tem perature decreases, the C oulomb blockade peaks become closer to each other, and ideally merge into a plateau at T = 0. This is due to the fact that the energy "0 itself is renormalized by the many body e ects, through the real part of the self energy. At very low tem perature we see that G 2e²=h (with maximum deviation of 10%) in the region in which the number of electrons is odd (n 1).

The same behavior is shown in Fig. 3b. Here we choose a smaller value of , so that the K ondo temperature is smaller. At high temperature we see again the two C oulom b blockade peaks, located at  $\ ^{0}_{0}$  0 and  $\ ^{0}_{0}$  U. At very low temperature the peaks approach each other and tend to the maximum value  $2e^{2}$ =h. However in this case the deviation from the limiting value is larger (about 25%). This is due to the fact that, because of the smaller  $T_{K}$ , down at T  $0.01T_{K}$  (about the lowest temperature that can be reached before the UNCA breaks down) we have (0) 0:75 instead of (0) = 1. Nevertheless, Fig. 3b reproduces the theoretical NRG calculations in the K ondo regime at several

(0) = 1. Nevertheless, Fig. 3b reproduces the theoretical NRG calculations in the K ondo regime at several di erent temperatures, see e.g. Fig. 3 in Ref. 21, Fig. 2 in Ref. 22, and Fig. 2a of Ref. 23. In addition, at high temperature Fig. 3b provides very good results in the whole range of "b.

It is worth to rem ind that when  $k_B\,T>$  the peak broadening is mainly due to therm ale ects. Thus, when we start from the high temperature regime and lower the temperature, at rst the peak width decreases. This e ect is shown in Fig. 3b. On the contrary, when  $k_B\,T$  the broadening is about 2 , in agreement with experimental results. Fig. 16 the Kondo temperature is negligibly small, lowering the temperature below  $=k_B$  does not produce any further change in the peak width. However, if the Kondo temperature is nite, as soon as  $k_B\,T$   $k_B\,T_K$  the two peaks tend to become broader, and merge in a single large peak at zero temperature. This e ect is shown in Fig. 3.

The UNCA results in Fig. 3 can be directly compared to the experimental measurements of the linear conductance vs the gate voltage. The curves in Fig. 3 reproduce very well the experiments described in Refs.  $2\{4,7,$  in which the measurement of the K ondo e ect in the equilibrium conductance of a QD+ leads system is reported. A green ent is satisfactory for the temperature dependence and the broadening of the peaks, and it covers the whole range of electron occupancy 0 n 2.

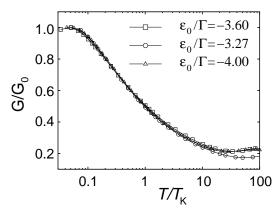


FIG.4. Universalbehavior of linear-response conductance norm alized to its saturation value  $G_0$ . The conductance is displayed as a function of  $T=T_{\rm K}$ , for three di erent values of " $_0=$  chosen in the K ondo regime. Param eters: = 0.275 m eV, D = 4 m eV, U = 2 m eV.

#### IV.SCALING BEHAVIOR

In diluted magnetic alloys, the low temperature (T  $T_K$ ) resistivity, (T), follows a universal scaling law, 1;35 i.e. = 0 = F (T= $T_K$ ), where 0 (T = 0) and F (x) is a function independent on system-related parameters. This happens because at low temperature and in the K ondo regime there is only one relevant energy scale,  $k_B$   $T_K$ . Similar scaling properties have been reported for the low temperature conductance of QD devices, 3;7;9;10 and carbon nanotubes. For a QD device described by the spin-1/2 Anderson model the universal function  $G=G_0$  was recently calculated by using the NRG. Here we calculate the same function by using the UNCA, and compare our results with the NRG calculations and experimental data.

# A . U niversal curves

The conductance calculated with the UNCA is shown in in Fig. 4 as a function of  $T\!=\!T_K$  . The di erent set of points correspond to dierent choices of "0=" in the K ondo regim e ("0 = 3.6 corresponds to the particlehole sym m etric point, that is  $"_0 = U = 2 = 1 \text{ m eV}$  in Fig. 3b). The conductance is normalized to  $G_0$   $G(T_0; V_q)$ , where  $T_0$  is the lowest temperature which can be reached before the UNCA breaks down. In order to achieve a universal behavior we de ne the K ondo tem perature such that G ( $T_K$ ) =  $G_0=2$ , as often done. The relative de-that is =  $(G_0 2e^2 = h) = (2e^2 = h)$ , depends on the choice of the param eters (we  $\mbox{nd}\ 2\% < \mbox{jj} < 25\%$  ). Figure 4 shows that the conductance follows the universal behavior in a fairly large range of temperatures. Departures from this universality are observed only for T

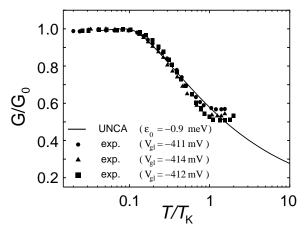


FIG.5. Experim ental data (Fig. 3c of Ref. 7) com pared with the UNCA universal curve  $G=G_0$ . Param eters of the theoretical curve:  $\textbf{"}_0==3.27$ , D = 4 m eV , U = 2 m eV . H ere  $V_{\text{ql}}$  is the gate voltage.

expected. We point out that at very low temperature (T=T $_{\rm K}$  1) the universal curve has the expected Ferm i liquid behavior, <sup>38</sup> i.e. (G  $_{\rm G_0}$ )=G $_{\rm O}$  / T $^{\rm 2}$ , while at higher temperature (T=T $_{\rm K}$  1) the conductance is proportional to ln (T=T $_{\rm K}$ ).

The universal curve of the conductance calculated with the UNCA is similar to NRG results for the ordinary K ondo problem (see e.g. Fig. 4 of Ref. 3 or Fig. 12 of Ref. 35) and to NRG results for the conductance in QD devices (see Figs. 4 and 7a of Ref. 22).

# B.Com parison with experim ents

The universal curve calculated here can be directly compared with existing measurements of the conductance. In this section we will compare in particular with the experimental data taken from Ref. 7. In Fig. 5 we show  $G=\!G_0$  vs  $T=\!T_K$ , and plot both the experimental points and our UNCA curve. In Ref. 7 the experimental data were normalized to  $\!G_0$ , the value of the conductance at the lowest temperature for which a measurement exists, and the K ondo temperature was defined as the temperature such that  $\!G$  ( $\!T_K$ ) =  $\!G_0=\!2$ .

We found the best agreem ents between UNCA and experiments for the choice  $"_0 = 327$ . Figure 5 shows that the crossover from the logarithm ic behavior to the low temperature Fermiliquid regime is reproduced fairly well by the conductance calculated by using the UNCA.

# C . Interpolation form ula

In order to extract the K ondo tem perature from experim ental data, it has become very common  $^{3;7;37}$  to the data with the empirical formula

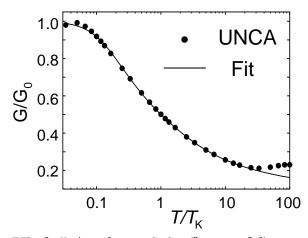


FIG. 6. Universal curve  $G=G_0$  (" $_0==3.6$ ) compared with the interpolation function given in Eq. (19). The resulting t parameters are:  $a=1=\ln{(1+b+c)}$  / 0.25, b=43.4 and c=10.25.

$$G (T) = G_0 \frac{T_K^{0}^2}{T^2 + T_K^{0}^2}$$
 (16)

where  $T_K^0 = T_K = 2^{1-s}$  1 and G ( $T_K$ ) =  $G_0$ =2. This formula reproduces well NRG results for  $T < T_K$  and has a single tting parameter, s. However, in the intermediate temperatures regime ( $T_K$ ) the exact conductance is proportional to  $T_K$ , as NRG calculations show,  $T_K^2$  and this behavior is not explicitly accounted for in formula (16). Here we propose an alternative phenomenological formula, which (a) is still quite simple, (b) reproduces fairly well the calculated conductance in the whole temperature regime and (c) shows explicitly the logarithm is behavior in the intermediate temperature regime. Our formula has two thing parameters instead of one.

W e notice that at very low tem perature, in the Ferm i liquid regime (T  $$T_K$ ), the conductance should show the Ferm i liquid T  $^2$  behavior,

$$G = G_0 \quad 1 \quad \frac{T^2}{T_K^2} \quad ;$$
 (17)

where is a param eter. Instead, at higher tem peratures (T  $\ T_K$  ) a logarithm ic behavior is expected

$$G / G_0 \ln (T = T_K)$$
: (18)

A function that satis es both requirem ents is the follow-ing

$$\frac{G}{G_0} = 1 + a \ln 1 + b \frac{T}{T_K}^2 + c \frac{T}{T_K}^{4^{\frac{4!}{1}}}; (19)$$

where a, b, and c are dimensionless parameters to be determined with best t techniques. By de ning  $T_{\rm K}$ 

as the tem perature such that  $G(T_K) = G_0=2$ , we nd  $a = 1 = \ln(1 + b + c)$ . Thus there are only two tting parameters in our formula.

In Fig. 6 we show the results of a t for the choice  $"_0 = 3.6$ . The empirical formula reproduces extrem ely well the UNCA results for the values b = 43.4, c = 10.25. These parameters slightly depend, of course, on the choice of  $"_0 = 1.0$ , and of the other UNCA parameters. Thus Eq. (19) reproduces the correct behavior, and it is physically correct both in the T  $T_K$  and T  $T_K$  regime. We notice that the fourth order term is required to reproduce the behavior of the conductance in the intermediate temperature regime, while the T $^2$  term is required to reproduce the low temperature Fermiliquid behavior.

#### V.CONCLUSION

In the present work we have calculated the conductance of a system made of a quantum dot coupled to two leads, described by the spin-1/2 Anderson model. We adopted the nite-U non-crossing approximation method (UNCA), which allowed us to calculate the conductance for the Anderson model with nite Coulomb repulsion. Thus we were able to study the conductance as a function of tem perature and gate voltage. We have shown that the results obtained with this method are in good agreement with those obtained by using the exact numerical renorm alization group (NRG). In addition we reproduced both the Coulomb blockade and the Kondo e ect in quantum dots. Inclusion of a nite Coulomb correlation is in portant in order to describe correctly the experim ental results in the whole regime of electron occupancies. The comparison with experimental data of Ref. 7 is fairly good, forwhat concerns both tem perature and gate voltage dependence. Finally we have suggested a simple phenomenological formula which ts UNCA results both in the logarithm ic and in the Ferm i-liquid temperature regions, reproducing very well also the crossover between them .

A lthough the spin-1/2 Anderson model can be solved by using the exact NRG, we believe that the UNCA is more suitable than NRG for extension to realistic systems, e.g. for taking into account the electronic structure of the dots, and thus we point out that the UNCA method can become an important tool to interpret the experiments. Possible applications are, for example, in the explanation of the Kondo elect in quantum dots for integer spin and the Kondo elect in carbon nanotubes. 37

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